

L Number	Hits	Search Text	DB	Time stamp
-	119259	438/\$.ccls. or 257/\$.ccls.	USPAT; US-PGPUB	2003/02/13 15:43
-	12479	((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide)(nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))	USPAT; US-PGPUB	2003/02/14 10:59
-	13765	((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub.4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))	USPAT; US-PGPUB	2003/02/13 15:47
-	4794	((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide)(nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))	USPAT; US-PGPUB	2003/02/14 10:53
-	11952	((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub.4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))	USPAT; US-PGPUB	2003/02/13 15:47
-	44	((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub.4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4")) and (uniform near3 thickness\$ near3 dielectric)	USPAT; US-PGPUB	2003/02/13 15:54
-	12	((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide)(nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no")) and (uniform near3 thickness\$ near3 dielectric)	USPAT; US-PGPUB	2003/02/13 16:04
-	35	((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub.4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4")) and (uniform near3 thickness\$ near3 dielectric)) not (((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitrogen trifluoronitride ammonia (nitrous adj oxide)(nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no")) and (uniform near3 thickness\$ near3 dielectric))	USPAT; US-PGPUB	2003/02/13 16:34
-	1	("6465373").PN.	USPAT; US-PGPUB	2003/02/13 16:35
-	0	((("6465373").PN.) and (implanting implanted implant)	USPAT; US-PGPUB	2003/02/13 16:59
-	36	((438/\$.ccls. or 257/\$.ccls.) and ((implanting implanted implant) with (nitriding nitridization))	USPAT; US-PGPUB	2003/02/13 17:46
-	4	RTN with (implanting implanted implant implantation)	USPAT; US-PGPUB	2003/02/13 17:47
-	255833	capacitor DRAM	USPAT; US-PGPUB	2003/02/14 10:54

-	122	(capacitor DRAM) and (((implanting implant implanted) with (angle)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide)(nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))	USPAT; US-PGPUB	2003/02/14 11:03
-	132	(capacitor DRAM) and (((implanting implant implanted) with (angle angled)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide)(nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))	USPAT; US-PGPUB	2003/02/14 15:45
-	10	((capacitor DRAM) and (((implanting implant implanted) with (angle angled)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide)(nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) not ((capacitor DRAM) and (((implanting implant implanted) with (angle)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide)(nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no")))	USPAT; US-PGPUB	2003/02/14 15:07
-	34	(capacitor DRAM) and (((doping doped dope) with (angle angled)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide)(nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))	USPAT; US-PGPUB	2003/02/14 14:04
-	242	(capacitor DRAM) and (((implanting implant implanted) with (angle angled)) same (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilane (silicon adj tetrachloride) "siF.sub.4" "siH.sub.4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))	USPAT; US-PGPUB	2003/02/14 15:23
-	15	((capacitor DRAM) and (((doping doped dope) with (angle angled)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide)(nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))) not ((capacitor DRAM) and (((implanting implant implanted) with (angle angled)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide)(nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no")))	USPAT; US-PGPUB	2003/02/14 14:06
-	170	((capacitor DRAM) and (((implanting implant implanted) with (angle angled)) same (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilane (silicon adj tetrachloride) "siF.sub.4" "siH.sub.4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4")) not ((capacitor DRAM) and (((implanting implant implanted) with (angle angled)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide)(nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no")))	USPAT; US-PGPUB	2003/02/14 14:46
-	180	(capacitor DRAM) and (((implanting implant implanted) same (angle angled)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide)(nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))	USPAT; US-PGPUB	2003/02/14 15:22
-	27	(uniform uniformity) with ((silicon adj nitride) "si.sub.3 N.sub.4") with (implanting implanted doped doping doped implant)	USPAT; US-PGPUB	2003/02/14 14:49

-	58	((capacitor DRAM) and (((implanting implant implanted) same (angle angled)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no")))) not ((capacitor DRAM) and (((implanting implant implanted) with (angle)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))))	USPAT; US-PGPUB	2003/02/14 15:04
-	135	(capacitor DRAM) and (((doping doped dope) same (angle angled)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))	USPAT; US-PGPUB	2003/02/14 15:17
-	304	(capacitor DRAM) and (((implanting implant implanted) same (angle angled)) same (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub.4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))	USPAT; US-PGPUB	2003/02/14 15:20
-	41	((capacitor DRAM) and (((implanting implant implanted) same (angle angled)) same (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub.4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4")))) not (((capacitor DRAM) and (((implanting implant implanted) with (angle angled)) same (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub.4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4")))) ((capacitor DRAM) and (((implanting implant implanted) with (angle)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no")))) (((capacitor DRAM) and (((implanting implant implanted) same (angle angled)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no")))) not ((capacitor DRAM) and (((implanting implant implanted) with (angle)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide) (nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))))	USPAT; US-PGPUB	2003/02/14 15:14
-	1	("6326277").PN.	USPAT; US-PGPUB	2003/02/14 15:14
-	1	((("6326277").PN.) and (silicon adj nitride)	USPAT; US-PGPUB	2003/02/14 15:15
-	311	(capacitor DRAM) and (((doped doping dope) same (angle angled)) same (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilande (silicon adj tetrachloride) "siF.sub.4" "siH.sub.4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "sicl.sub.4"))	USPAT; US-PGPUB	2003/02/14 15:19

-	203	((capacitor DRAM) and (((doped doping dope) same (angle angled)) same (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilane (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "siCl.sub.4")))) not ((capacitor DRAM) and (((implanting implant implanted) same (angle angled)) same (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilane (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "siCl.sub.4"))))	USPAT; US-PGPUB	2003/02/14 15:20
-	74	((capacitor DRAM) and (((doping doped dope) same (angle angled)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide)(nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no")))) not ((capacitor DRAM) and (((implanting implant implanted) same (angle angled)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide)(nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))))	USPAT; US-PGPUB	2003/02/14 15:21
-	203	((capacitor DRAM) and (((doped doping dope) same (angle angled)) same (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilane (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "siCl.sub.4")))) not ((capacitor DRAM) and (((implanting implant implanted) same (angle angled)) same (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilane (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "siCl.sub.4"))))) not ((capacitor DRAM) and (((implanting implant implanted) with (angle angled)) same (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilane (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "siCl.sub.4"))))	USPAT; US-PGPUB	2003/02/14 15:23
-	198	((capacitor DRAM) and (((doped doping dope) same (angle angled)) same (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilane (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "siCl.sub.4")))) not ((capacitor DRAM) and (((implanting implant implanted) same (angle angled)) same (silicon (silicon adj tetrafluoride) silane dichlorosilane trichlorosilane (silicon adj tetrachloride) "siF.sub.4" "siH.sub4" "siH.sub.2 cl.sub.2" "siCl.sub.3" "siCl.sub.4"))))) not ((capacitor DRAM) and (((implanting implant implanted) same (angle angled)) same (nitrogen trifluoronitride ammonia (nitrous adj oxide)(nitric adj oxide) "n.sub.2" "nf.sub.3" "nh.sub.3" "n.sub.2 o" "no"))))	USPAT; US-PGPUB	2003/02/14 15:24
-	1	09/385787	USPAT; US-PGPUB	2003/02/14 15:32
-	1	("6159785").PN.	USPAT; US-PGPUB	2003/02/14 15:32
-	1	((("6159785").PN.) and (silicon adj nitride)	USPAT; US-PGPUB	2003/02/14 15:32

-	3	(capacitor DRAM) and (((implanting implant implanted dope doping doped) with (angle angled)) same (nitrogen "si.sub.3 n.sub.4") same (uniformity uniform))	USPAT; US-PGPUB	2003/02/14 15:47
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